

isc Silicon PNP Power Transistor

2SB1182

DESCRIPTION

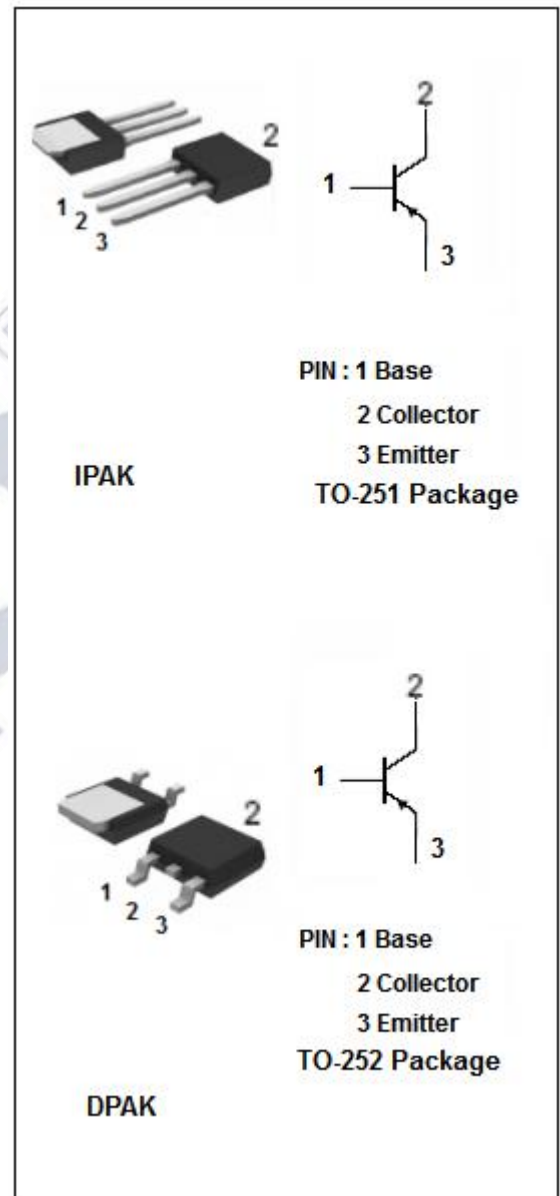
- Small and slim package
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Power dissipation

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-32	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current-Continuous	-2	A
P _C	Collector Power Dissipation @ T _C =25°C	1.5	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



isc Silicon PNP Power Transistor**2SB1182****ELECTRICAL CHARACTERISTICS** $T_c=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -2\text{A}; I_B = -200\text{mA}$			-0.8	V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -50\mu\text{A}; I_B = 0$	-40			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -1\text{mA}; I_B = 0$	-32			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -50\mu\text{A}; I_C = 0$	-6			V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -20\text{V}; I_E = 0$			-1.0	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -4\text{V}; I_C = 0$			-1.0	μA
h_{FE}	DC Current Gain	$I_C = -0.5\text{A}; V_{CE} = -3\text{V}$	82		390	
C_{OB}	Output Capacitance	$I_E = 0; V_{CB} = -10\text{V}; f = 1.0\text{MHz}$		50		pF
f_T	Current-Gain—Bandwidth Product	$I_C = -500\text{mA}; V_{CE} = -5\text{V}$		100		MHz

◆ **h_{FE} Classifications**

P	Q	R
82-180	120-270	180-390

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Outline Drawing

